

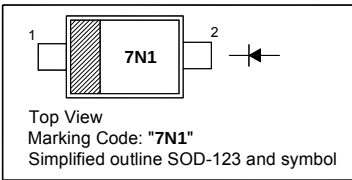
SDB17W

Silicon Epitaxial Planar Schottky Barrier Diode

For high frequency rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

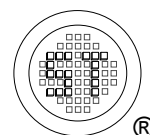
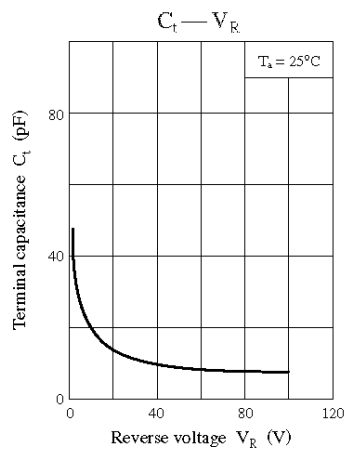
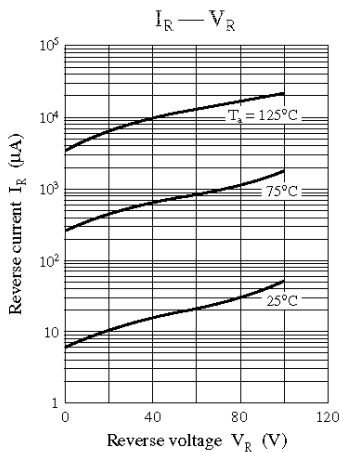
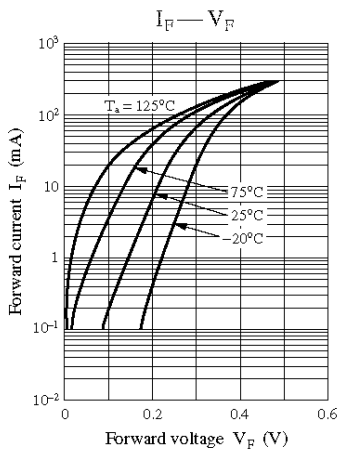


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	100	V
Average Forward Rectified Current	$I_{F(AV)}$	300	mA
Non-repetitive Peak Forward Surge Current (at $t = 10\text{ ms}$)	I_{FSM}	1.5	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 300\text{ mA}$	V_F	-	-	0.58	V
Reverse Breakdown Voltage at $I_R = 50\text{ }\mu\text{A}$	$V_{(BR)R}$	100	-	-	V
Reverse Current at $V_R = 100\text{ V}$	I_R	-	-	200	μA
Terminal Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_T	-	100	-	pF
Reverse Recovery Time at $I_F = I_R = 100\text{ mA}$, $I_{rr} = 0.1\text{ }I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	7	-	ns

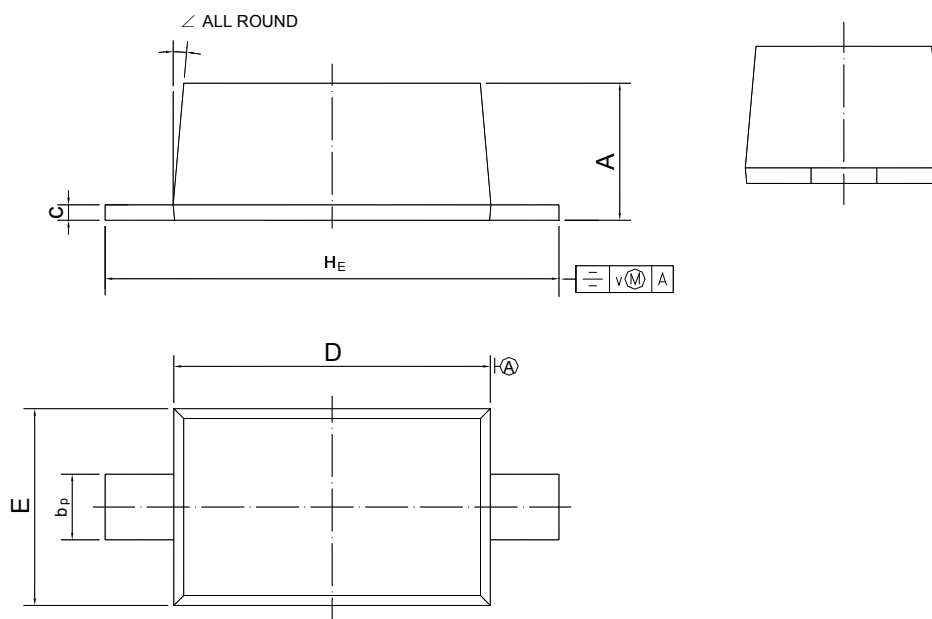


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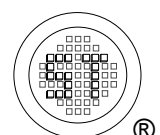
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°



Dated : 17/09/2009